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#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	24
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN
Supplier Device Package	28-UFQFPN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l011g4u6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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# 2 Description

The access line ultra-low-power STM32L011x3/4 family incorporates the high-performance ARM<sup>®</sup> Cortex<sup>®</sup>-M0+ 32-bit RISC core operating at a 32 MHz frequency, high-speed embedded memories (up to 16 Kbytes of Flash program memory, 512 bytes of data EEPROM and 2 Kbytes of RAM) plus an extensive range of enhanced I/Os and peripherals.

The STM32L011x3/4 devices provide high power efficiency for a wide range of performance. It is achieved with a large choice of internal and external clock sources, an internal voltage adaptation and several low-power modes.

The STM32L011x3/4 devices offer several analog features, one 12-bit ADC with hardware oversampling, two ultra-low-power comparators, several timers, one low-power timer (LPTIM), three general-purpose 16-bit timers, one RTC and one SysTick which can be used as timebases. They also feature two watchdogs, one watchdog with independent clock and window capability and one window watchdog based on bus clock.

Moreover, the STM32L011x3/4 devices embed standard and advanced communication interfaces: one I2C, one SPI, one USART, and a low-power UART (LPUART).

The STM32L011x3/4 also include a real-time clock and a set of backup registers that remain powered in Standby mode.

The ultra-low-power STM32L011x3/4 devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +125 °C temperature range. A comprehensive set of power-saving modes allows the design of low-power applications.







Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage ( $V_{REFINT}$ ) in Stop mode. The device remains in reset mode when  $V_{DD}$  is below a specified threshold,  $V_{POR/PDR}$  or  $V_{BOR}$ , without the need for any external reset circuit.

Note: The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the startup time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The devices feature an embedded programmable voltage detector (PVD) that monitors the  $V_{DD/VDDA}$  power supply and compares it to the  $V_{PVD}$  threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when  $V_{DD/VDDA}$  drops below the  $V_{PVD}$  threshold and/or when  $V_{DD/VDDA}$  is higher than the  $V_{PVD}$  threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

#### 3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32 KHz oscillator, RCC\_CSR).

#### 3.4.4 Boot modes

At startup, BOOT0 pin and nBOOT0, nBOOT1 and nBOOT\_SEL option bits are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1 (PA4, PA7, PA13 and PA14 on TSSOP14 package or PA4, PA5, PA6 and PA7 on other packages) or USART2 (PA2, PA3 and PA9, PA10). See STM32<sup>™</sup> microcontroller system memory boot mode AN2606 for details.





Figure 2. Clock tree

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(rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 38 GPIOs can be connected to the 16 configurable interrupt/event lines. The 10 other lines are connected to PVD, RTC, USART, I2C, LPUART, LPTIM or comparator events.

## 3.8 Memories

The STM32L011x3/4 devices have the following features:

- 2 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 8 or 16 Kbytes of embedded Flash program memory
  - 512 bytes of data EEPROM
  - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no protection
- Level 1: memory readout protected.

The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected

• Level 2: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The whole non-volatile memory embeds the error correction code (ECC) feature.

### 3.9 Direct memory access (DMA)

The flexible 5-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I<sup>2</sup>C, USART, LPUART, general-purpose timers, and ADC.

## 3.12 Ultra-low-power comparators and reference voltage

The STM32L011x3/4 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
  - External I/O pins
  - Internal reference voltage (V<sub>REFINT</sub>)
  - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1  $\mu$ A typical).

# 3.13 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21 and LPTIM1 timer input captures. It also controls the routing of internal analog signals to the ADC, COMP1 and COMP2 and the internal reference voltage  $V_{\text{REFINT}}$ .

# 3.14 Timers and watchdogs

The ultra-low-power STM32L011x3/4 devices include two general-purpose timers, one low-power timer (LPTIM1), two watchdog timers and the SysTick timer.

*Table 7* compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No

 Table 7. Timer feature comparison



### 3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 37 kHz internal RC and, as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

### 3.14.5 Window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

# 3.15 Communication interfaces

# 3.15.1 I<sup>2</sup>C bus

One I<sup>2</sup>C interface (I2C1) can operate in multimaster or slave modes. The I<sup>2</sup>C interface can support Standard mode (Sm, up to 100 kbit/s), Fast mode (Fm, up to 400 kbit/s) and Fast Mode Plus (Fm+, up to 1 Mbit/s) with 20 mA output drive on some I/Os.

The I<sup>2</sup>C interface supports 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask). They also include programmable analog and digital noise filters.

	Analog filter	Digital filter
Pulse width of suppressed spikes	≥ 50 ns	Programmable length from 1 to 15 I2C peripheral clocks
Benefits	Available in Stop mode	<ol> <li>Extra filtering capability vs. standard requirements.</li> <li>Stable length</li> </ol>
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

Table 8.	Comparison	of I2C analoc	and digital	filters
	oompanoon		j ana aigitai	

In addition, I2C1 provides hardware support for SMBus 2.0 and PMBus 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. I2C1 also has a clock domain independent from the CPU clock, allowing the I2C1 to wake up the MCU from Stop mode on address match.

The I2C interface can be served by the DMA controller.

Refer to *Table 9* for the supported modes and features of I2C interface.



# 6 Electrical characteristics

# 6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V<sub>SS</sub>.

#### 6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A = 25$  °C and  $T_A = T_Amax$  (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$ ).

#### 6.1.2 Typical values

Unless otherwise specified, typical data are based on T<sub>A</sub> = 25 °C, V<sub>DD</sub> = 3.6 V (for the 1.65 V  $\leq$  V<sub>DD</sub>  $\leq$  3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$ ).

#### 6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

#### 6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

#### 6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.





# 6.3 Operating conditions

# 6.3.1 General operating conditions

Table 16. General operating conditions	Table	18.	General	operating	conditions
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Symbol	Parameter	Conditions	Min	Мах	Unit	
f <sub>HCLK</sub>	Internal AHB clock frequency	-	0	32		
f <sub>PCLK1</sub>	Internal APB1 clock frequency	-	0	32	MHz	
f <sub>PCLK2</sub>	Internal APB2 clock frequency	-	0	32		
		BOR detector disabled	1.65	3.6		
V <sub>DD</sub>	Standard operating voltage	BOR detector enabled, at power on	1.8	3.6	V	
		BOR detector disabled, after power on	1.65	3.6		
V <sub>DDA</sub>	Analog operating voltage (all features)	Must be the same voltage as $V_{DD}^{(1)}$	1.65	3.6	V	
	Input voltage on ET ETf and PST pins <sup>(2)</sup>	$2.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.6 \text{ V}$	-0.3	5.5		
V		1.65 V ≤ V <sub>DD</sub> ≤2.0 V	-0.3	5.2	V	
V IN	Input voltage on BOOT0 pin	-	0	5.5		
	Input voltage on TC pin	-	-0.3	V <sub>DD</sub> +0.3		
		LQFP32 package	-	333		
		UFQFPN32 package	-	513		
	Power dissipation at $T_A = 85 \degree C$ (range 6) or $T_A = 105 \degree C$ (rage 7) <sup>(3)</sup>	UFQFPN28 package	-	206		
		WLCSP25 package	-	286		
		TSSOP20 package	-	270		
		UFQFPN20 package	-	196		
D		TSSOP14 package	-	210	m\//	
PD		LQFP32 package	-	83	11100	
		UFQFPN32 package	-	128		
		UFQFPN28 package	-	52		
	Power dissipation at $T_A = 125$ °C (range 3) <sup>(3)</sup>	WLCSP25 package	-	71		
	-,	TSSOP20 package	-	67		
		UFQFPN20 package	-	49		
		TSSOP14 package	-	53		



## 6.3.3 Embedded internal reference voltage

The parameters given in *Table 21* are based on characterization results, unless otherwise specified.

Table 20. Embedded internal reference voltage calibration values				
Calibration value name	Description	Memory address		
/REFINT_CAL	Raw data acquired at temperature of 25°C V <sub>DDA</sub> = 3 V	0x1FF8 0078 - 0x1FF8 0079		

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>REFINT out</sub> <sup>(2)</sup>	Internal reference voltage	– 40 °C < T <sub>J</sub> < +125 °C	1.202	1.224	1.242	V
T <sub>VREFINT</sub>	Internal reference startup time	-	-	2	3	ms
V <sub>VREF_MEAS</sub>	V <sub>DDA</sub> voltage during V <sub>REFINT</sub> factory measure	-	2.99	3	3.01	V
A <sub>VREF_MEAS</sub>	Accuracy of factory-measured V <sub>REFINT</sub> value <sup>(3)</sup>	Including uncertainties due to ADC and V <sub>DDA</sub> values	-	-	±5	mV
т(4)	Temperature coefficient	–40 °C < T <sub>J</sub> < +125 °C	-	25	100	nnm/°C
<sup>I</sup> Coeff` ′		0 °C < T <sub>J</sub> < +50 °C	-	-	20	ppin/ C
A <sub>Coeff</sub> <sup>(4)</sup>	Long-term stability	1000 hours, T= 25 °C	-	-	1000	ppm
V <sub>DDCoeff</sub> <sup>(4)</sup>	Voltage coefficient	3.0 V < V <sub>DDA</sub> < 3.6 V	-	-	2000	ppm/V
T <sub>S_vrefint</sub> <sup>(4)(5)</sup>	ADC sampling time when reading the internal reference voltage	-	5	10	-	μs
T <sub>ADC_BUF</sub> <sup>(4)</sup>	Startup time of reference voltage buffer for ADC	-	-	-	10	μs
I <sub>BUF_ADC</sub> <sup>(4)</sup>	Consumption of reference voltage buffer for ADC	-	-	13.5	25	μA
I <sub>VREF_OUT</sub> <sup>(4)</sup>	VREF_OUT output current <sup>(6)</sup>	-	-	-	1	μA
C <sub>VREF_OUT</sub> <sup>(4)</sup>	VREF_OUT output load	-	-	-	50	pF
I <sub>LPBUF</sub> <sup>(4)</sup>	Consumption of reference voltage buffer for VREF_OUT and COMP	-	-	730	1200	nA
V <sub>REFINT_DIV1</sub> <sup>(4)</sup>	1/4 reference voltage	-	24	25	26	
V <sub>REFINT_DIV2</sub> <sup>(4)</sup>	1/2 reference voltage	-	49	50	51	% Vdeeinit
V <sub>REFINT_DIV3</sub> <sup>(4)</sup>	3/4 reference voltage	-	74	75	76	REFINI

#### Table 21. Embedded internal reference voltage<sup>(1)</sup>

1. Refer to *Table 33: Peripheral current consumption in Stop and Standby mode* for the value of the internal reference current consumption (I<sub>REFINT</sub>).

2. Guaranteed by test in production.

3. The internal V<sub>REF</sub> value is individually measured in production and stored in dedicated EEPROM bytes.

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Symbol	Parameter	Co	nditions	f <sub>HCLK</sub>	Тур	Max <sup>(1)</sup>	Unit
				1 MHz	140	180	μA
			Range 3, $V_{CORE}$ =1.2 V	2 MHz	245	290	
				4 MHz	460	540	
		f <sub>HSE</sub> = f <sub>HCLK</sub> up to		4 MHz	0.56	0.65	
Supply I <sub>DD</sub> current in (Run Run mode, from code Flash) executed from Flash		16 MHz included, f <sub>HSE</sub> = f <sub>HCLK</sub> /2 above 16 MHz (PLL ON) <sup>(2)</sup>	Range 2, V <sub>CORE</sub> =1.5 V, VOS[1:0]=10.	8 MHz	1.1	1.3	- mA
	Supply current in Run mode,			16 MHz	2.1	2.4	
			Range 1, V <sub>CORE</sub> =1.8 V, VOS[1:0]=01	8 MHz	1.3	1.6	
				16 MHz	2.6	3	
	executed			32 MHz	5.3	6.5	
	from Flash			65 kHz	34.5	54	
	MSI clock	Range 3, V <sub>CORE</sub> =1.2 V, VOS[1:0]=11	524 kHz	86	120	μA	
				4.2 MHz 505	560		
			Range 2, V <sub>CORE</sub> =1.5 V, VOS[1:0]=10,	16 MHz	2.2	2.6	m (
		HSI clock -	Range 1, V <sub>CORE</sub> =1.8 V, VOS[1:0]=01	32 MHz	5.4	5.9	

Table 22. Current consum	ption in Run mode, co	ode with data processi	ng running from Flash
	puon in ruan ino ao, o	040 mm 4444 p. 00000.	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).

Table 23. Current consumption in Run mode vs code type,
code with data processing running from Flash

Symbol	Parameter		Conditions		f <sub>HCLK</sub>	Тур	Unit
Supply I <sub>DD</sub> current in (Run Run mode.				Dhrystone		460	
		Range 3, V <sub>CORE</sub> =1.2 V, VOS[1:0]=11	CoreMark		440	μA	
			Fibonacci	4 MHz	330		
			while(1)		305		
	current in Run mode,	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above		while(1), prefetch OFF		320	
from Flash)	code			Dhrystone		5.4	mA
1 10311)	from Flash			CoreMark	1	4.9	
			Range 1, VOS[1:0]=01,	Fibonacci	32 MHz	5	
			V <sub>CORE</sub> =1.8 V	while(1)		4.35	
				while(1), prefetch OFF		3.7	

1. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).





Figure 17. I<sub>DD</sub> vs V<sub>DD</sub>, at T<sub>A</sub>= -40/25/55/ 85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

#### Table 28. Current consumption in Low-power Sleep mode

Symbol	Parameter	Conditions			Тур	Max <sup>(1)</sup>	Unit
			MSI clock, 65 kHz f <sub>HCLK</sub> = 32 kHz Flash OFF	$T_A = -40 \ ^\circ C$ to 25 $^\circ C$	2.5 <sup>(2)</sup>	-	
			MSI clock, 65 kHz f <sub>HCLK</sub> = 32 kHz Flash ON	$T_A$ = -40 °C to 25 °C	13	19	
				T <sub>A</sub> = 85 °C	15.5	20	
				T <sub>A</sub> = 105 °C	17.5	22	
		All peripherals OFF, V <sub>DD</sub> from 1.65 V to 3.6 V		T <sub>A</sub> = 125 °C	21	29	
	Supply		MSI clock, 65 kHz f <sub>HCLK</sub> = 65 kHz, Flash ON	$T_A$ = -40 °C to 25 °C	13.5	19	
I <sub>DD</sub> (LP Sleep)	Low-power			T <sub>A</sub> = 85 °C	16	20	μA
	sleep mode			T <sub>A</sub> = 105 °C	18	22	
				T <sub>A</sub> = 125 °C	21.5	29	
				$T_A$ = -40 °C to 25 °C	15.5	21	
			MSI clock. 131 kHz	T <sub>A</sub> = 55 °C	17	22	
			$f_{HCLK} = 131 \text{ kHz},$ Flash ON	T <sub>A</sub> = 85 °C	18	23	
				T <sub>A</sub> = 105 °C	19.5	24	
				T <sub>A</sub> = 125 °C	23.5	31	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.

2. As the CPU is in Sleep mode, the difference between the current consumption with Flash memory ON and OFF (nearly 12  $\mu$ A) is the same whatever the clock frequency.



#### Low-speed external user clock generated from an external source

The characteristics given in the following table result from tests performed using a lowspeed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 18*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSE_ext</sub>	User external clock source frequency		-	32.768	1000	kHz
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage		0.7V <sub>DD</sub>	-	V <sub>DD</sub>	V
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	-	V <sub>SS</sub>	-	0.3V <sub>DD</sub>	v
t <sub>w(LSE)</sub> t <sub>w(LSE)</sub>	OSC32_IN high or low time		465	-	-	ne
t <sub>r(LSE)</sub> t <sub>f(LSE)</sub>	OSC32_IN rise or fall time		-	-	10	115
C <sub>IN(LSE)</sub>	OSC32_IN input capacitance	-	-	0.6	-	pF
DuCy <sub>(LSE)</sub>	Duty cycle	-	45	-	55	%
١L	OSC32_IN Input leakage current	$V_{SS} \le V_{IN} \le V_{DD}$	-	-	±1	μA

Table 36. Low-speed external user clock characteristics<sup>(1)</sup>

1. Guaranteed by design, not tested in production





#### Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 37*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization





Figure 29. Typical connection diagram using the ADC

- 1. Refer to Table 54: ADC characteristics for the values of RAIN, RADC and CADC.
- C<sub>parasitic</sub> represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high C<sub>parasitic</sub> value will downgrade conversion accuracy. To remedy this, f<sub>ADC</sub> should be reduced.

#### 6.3.16 Temperature sensor characteristics

#### Table 57. Temperature sensor calibration values

Calibration value name	Description	Memory address	
TS_CAL2	TS ADC raw data acquired at temperature of 130 °C $\pm$ 5 °C, V <sub>DDA</sub> = 3 V $\pm$ 10 mV	0x1FF8 007E - 0x1FF8 007F	

	•				
Symbol	Parameter	Min	Тур	Мах	Unit
T <sub>L</sub> <sup>(1)</sup>	V <sub>SENSE</sub> linearity with temperature	-	±1	±2	°C
Avg_Slope <sup>(1)</sup>	Average slope	1.48	1.61	1.75	mV/°C
V <sub>130</sub>	Voltage at 130°C ±5°C <sup>(2)</sup>	640	670	700	mV
I <sub>DDA(TEMP)</sub> <sup>(3)</sup>	Current consumption	-	3.4	6	μA
t <sub>START</sub> <sup>(3)</sup>	Startup time	-	-	10	
T <sub>S_temp</sub> <sup>(4)(3)</sup>	ADC sampling time when reading the temperature	10	-	-	μs

Table 58. Temperature sensor characteristics

1. Guaranteed by characterization results, not tested in production.

2. Measured at V<sub>DD</sub> = 3 V  $\pm$ 10 mV. V30 ADC conversion result is stored in the TS\_CAL1 byte.

3. Guaranteed by design, not tested in production.

4. Shortest sampling time can be determined in the application by multiple iterations.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode			8	
f <sub>SCK</sub> 1/t <sub>c(SCK)</sub>	SPI clock frequency	Slave mode Transmitter 1.65 <v<sub>DD&lt;3.6V</v<sub>	-	-	8	MHz
		Slave mode Transmitter 2.7 <v<sub>DD&lt;3.6V</v<sub>			8 <sup>(2)</sup>	
Duty <sub>(SCK)</sub>	Duty cycle of SPI clock frequency	cycle of SPI clock frequency Slave mode		50	70	%
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI presc = 2	4Tpclk	-	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI presc = 2	2Tpclk	-	-	
t <sub>w(SCKH)</sub> t <sub>w(SCKL)</sub>	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t <sub>su(MI)</sub>	Data input actus tima	Master mode	3	-	-	
t <sub>su(SI)</sub>	Data input setup time	Slave mode		-	-	
t <sub>h(MI)</sub>	Data input hold time	Master mode	6	-	-	
t <sub>h(SI)</sub>	Data input hold time	Slave mode	2	-	-	ns
t <sub>a(SO</sub>	Data output access time	Slave mode	18	-	52	
t <sub>dis(SO)</sub>	Data output disable time	Slave mode	12	-	42	
turee	Data output valid time	Slave mode	-	16	33	
•v(SO)		Master mode	-	4	6	
t <sub>v(MO)</sub>	Data output hold time	Slave mode	11	-	-	1
t <sub>h(SO)</sub>	Data output noid time	Master mode	3	-	-	1

<b>-</b>					_	~ (	1)
lable 66.	SPI	characteristics	ın	voltage	Range	2 \	•,

1. Guaranteed by characterization results, not tested in production.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of  $t_{v(SO)}$  and  $t_{su(MI)}$  which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having  $t_{su(MI)} = 0$  while Duty<sub>(SCK)</sub> = 50%.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>scк</sub>		Master mode			2	
1/t <sub>c(SCK)</sub>	SPI Clock liequency	Slave mode	-	-	2 <sup>(2)</sup>	
Duty <sub>(SCK)</sub>	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI presc = 2	4Tpclk	-	-	
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI presc = 2	2Tpclk	-	-	
t <sub>w(SCKH)</sub> t <sub>w(SCKL)</sub>	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
t <sub>su(MI)</sub>	Data input actur timo	Master mode	3	-	-	
t <sub>su(SI)</sub>	Data input setup time	Slave mode	3	-	-	
t <sub>h(MI)</sub>	Data input hold time	Master mode	16	-	-	
t <sub>h(SI)</sub>		Slave mode	14	-	-	ns
t <sub>a(SO</sub>	Data output access time	Slave mode	30	-	70	
t <sub>dis(SO)</sub>	Data output disable time	Slave mode	40	-	80	
t (ee)	Data output valid time	Slave mode	-	26.5	47	
v(SO)		Master mode	-	4	6	
t <sub>v(MO)</sub>	Dete autout hald time	Slave mode	20	-	-	1
t <sub>h(SO)</sub>		Master mode	3	-	-	1

Table 67	SPI cl	haractoristics	in	voltano	Rango	z (1)	
Table 07.	SFIC	laracteristics	ш	vonage	капуе	S` '	

1. Guaranteed by characterization results, not tested in production.

2. The maximum SPI clock frequency in slave transmitter mode is determined by the sum of  $t_{v(SO)}$  and  $t_{su(MI)}$  which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having  $t_{su(MI)} = 0$  while Duty<sub>(SCK)</sub> = 50%.



Figure 30. SPI timing diagram - slave mode and CPHA = 0

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#### LQFP32 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

# 7.3 WLCSP25 package information



# Figure 39. WLCSP25 - 25-ball, 2.133 x 2.070 mm, 0.4 mm pitch wafer level chip scale package outline

1. Drawing is not to scale.

Table 70. WLCSP25 - 25-ball, 2.133 x 2.070 mm, 0.4 mm pitch wafer level chip scale
package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>			
Symbol	Min	Тур	Мах	Min	Тур	Max	
А	0.525	0.555	0.585	0.0207	0.0219	0.0230	
A1	-	0.175	-	-	0.0069	-	
A2	-	0.380	-	-	0.0150	-	
A3 <sup>(2)</sup>	-	0.025	-	-	0.0010	-	
b <sup>(3)</sup>	0.220	0.250	0.280	0.0087	0.0098	0.0110	
D	2.098	2.133	2.168	0.0826	0.0840	0.0854	
E	2.035	2.070	2.105	0.0801	0.0815	0.0829	
е	-	0.400	-	-	0.0157	-	
e1	-	1.600	-	-	0.0630	-	
e2	-	1.600	-	-	0.0630	-	
F	-	0.2665	-	-	0.0105	-	



# Table 70. WLCSP25 - 25-ball, 2.133 x 2.070 mm, 0.4 mm pitch wafer level chip scale package mechanical data (continued)

G	-	0.235	-	-	0.0093	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
CCC	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

2. Back side coating.

3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

# Figure 40. WLCSP25 - 25-ball, 2.133 x 2.070 mm, 0.4 mm pitch wafer level chip scale package recommended footprint



WLCSP25\_A05M\_FP\_V1

#### Table 71. WLCSP25 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values		
Pitch	0.4 mm		
Dpad	0.225 mm		
Dsm	0.290 mm typ. (depends on the soldermask registration tolerance)		
Stencil opening	0.250 mm		
Stencil thickness	0.100 mm		



# 7.6 TSSOP20 package information





1. Drawing is not to scale.

Table 74. TSSOP20 – 20-lead thin shrink small outline,	6.5 x 4.4 mm, 0.65 mm pitch,
package mechanical data	

Symbol	millimeters		inches <sup>(1)</sup>			
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
С	0.090	-	0.200	0.0035	-	0.0079
D	6.400	6.500	6.600	0.2520	0.2559	0.2598
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1	4.300	4.400	4.500	0.1693	0.1732	0.1772
е	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-

